

PNP general purpose transistors

BC856; BC857

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 65 V).

APPLICATIONS

- General purpose switching and amplification.

DESCRIPTION

PNP transistor in a SOT23 plastic package.
NPN complements: BC846 and BC847.

MARKING

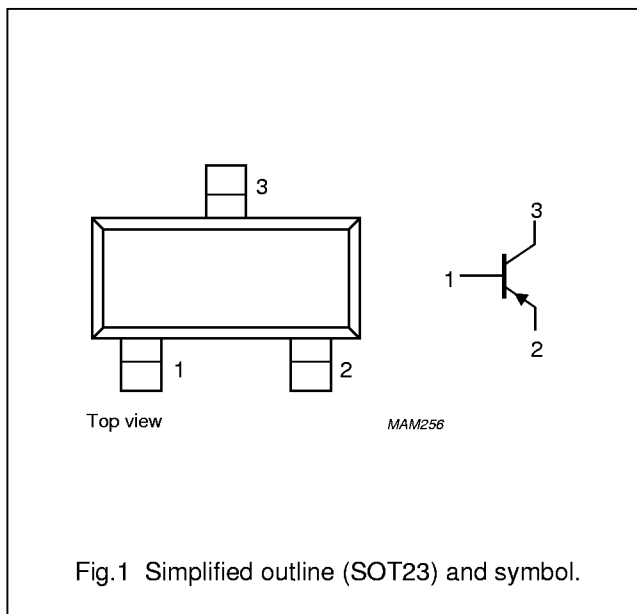
TYPE NUMBER	MARKING CODE ⁽¹⁾	TYPE NUMBER	MARKING CODE ⁽¹⁾
BC856	3D*	BC857A	3E*
BC856A	3A*	BC857B	3F*
BC856B	3B*	BC857C	3G*
BC857	3H*		

Note

1. * = p : Made in Hong Kong.
* = t : Made in Malaysia.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter			
	BC856		—	–80	V
	BC857		—	–50	V
V_{CEO}	collector-emitter voltage	open base			
	BC856		—	–65	V
	BC857		—	–45	V
V_{EBO}	emitter-base voltage	open collector	—	–5	V
I_C	collector current (DC)		—	–100	mA
I_{CM}	peak collector current		—	–200	mA
I_{BM}	peak base current		—	–200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$; note 1	—	250	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		—	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

Note

1. Mounted on an FR4 printed-circuit board.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Mounted on an FR4 printed-circuit board.

CHARACTERISTICS

$T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

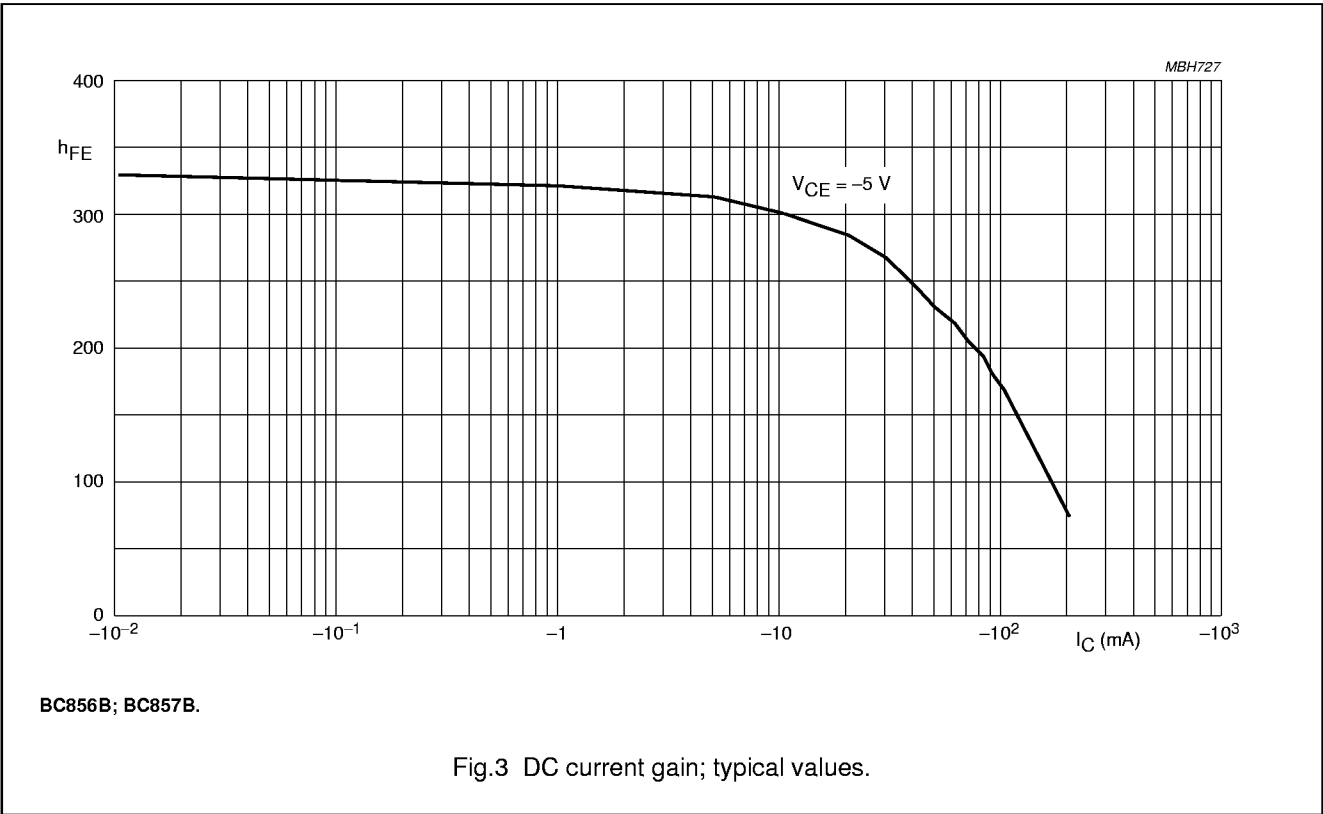
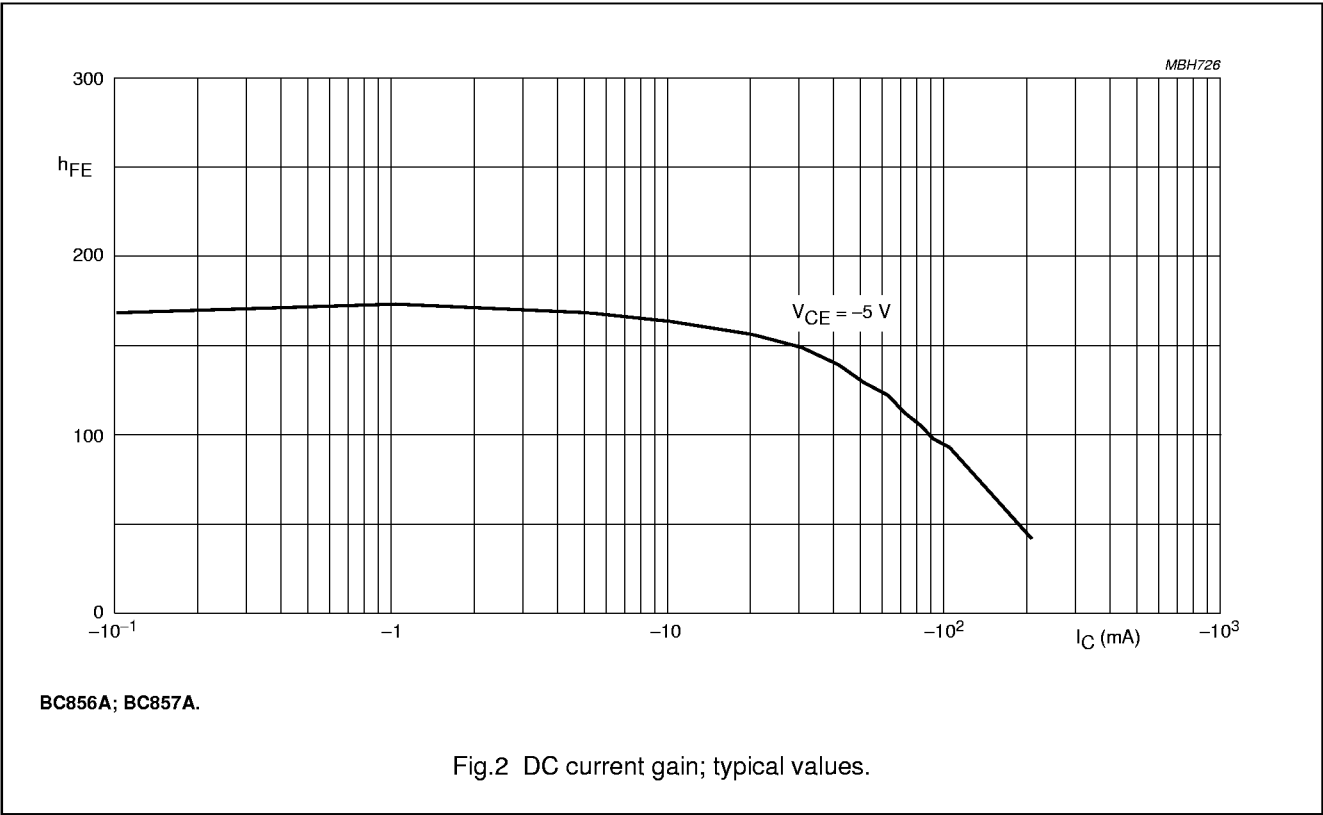
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = -30\text{ V}$	–	–1	–15	nA
		$I_E = 0; V_{CB} = -30\text{ V}; T_j = 150\text{ }^{\circ}\text{C}$	–	–	–4	μA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = -5\text{ V}$	–	–	100	nA
h_{FE}	DC current gain BC856 BC857 BC856A; BC857A BC856B; BC857B BC857C	$I_C = -2\text{ mA}; V_{CE} = -5\text{ V};$ see Figs 2, 3 and 4	125	–	475	
			125	–	800	
			125	–	250	
			220	–	475	
			420	–	800	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -10\text{ mA}; I_B = -0.5\text{ mA}$	–	–75	–300	mV
		$I_C = -100\text{ mA}; I_B = -5\text{ mA}$	–	–250	–650	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = -10\text{ mA}; I_B = -0.5\text{ mA};$ note 1	–	–700	–	mV
		$I_C = -100\text{ mA}; I_B = -5\text{ mA};$ note 1	–	–850	–	mV
V_{BE}	base-emitter voltage	$I_C = -2\text{ mA}; V_{CE} = -5\text{ V};$ note 2	–600	–650	–750	mV
		$I_C = -10\text{ mA}; V_{CE} = -5\text{ V};$ note 2	–	–	–820	mV
C_c	collector capacitance	$I_E = I_C = 0; V_{CB} = -10\text{ V}; f = 1\text{ MHz}$	–	4.5	–	pF
f_T	transition frequency	$I_C = -10\text{ mA}; V_{CE} = -5\text{ V};$ $f = 100\text{ MHz}$	100	–	–	MHz
F	noise figure	$I_C = -200\text{ }\mu\text{A}; V_{CE} = -5\text{ V};$ $R_S = 2\text{ k}\Omega; f = 1\text{ kHz}; B = 200\text{ Hz}$	–	2	10	dB

Notes

1. V_{BEsat} decreases by about -1.7 mV/K with increasing temperature.
2. V_{BE} decreases by about -2 mV/K with increasing temperature.

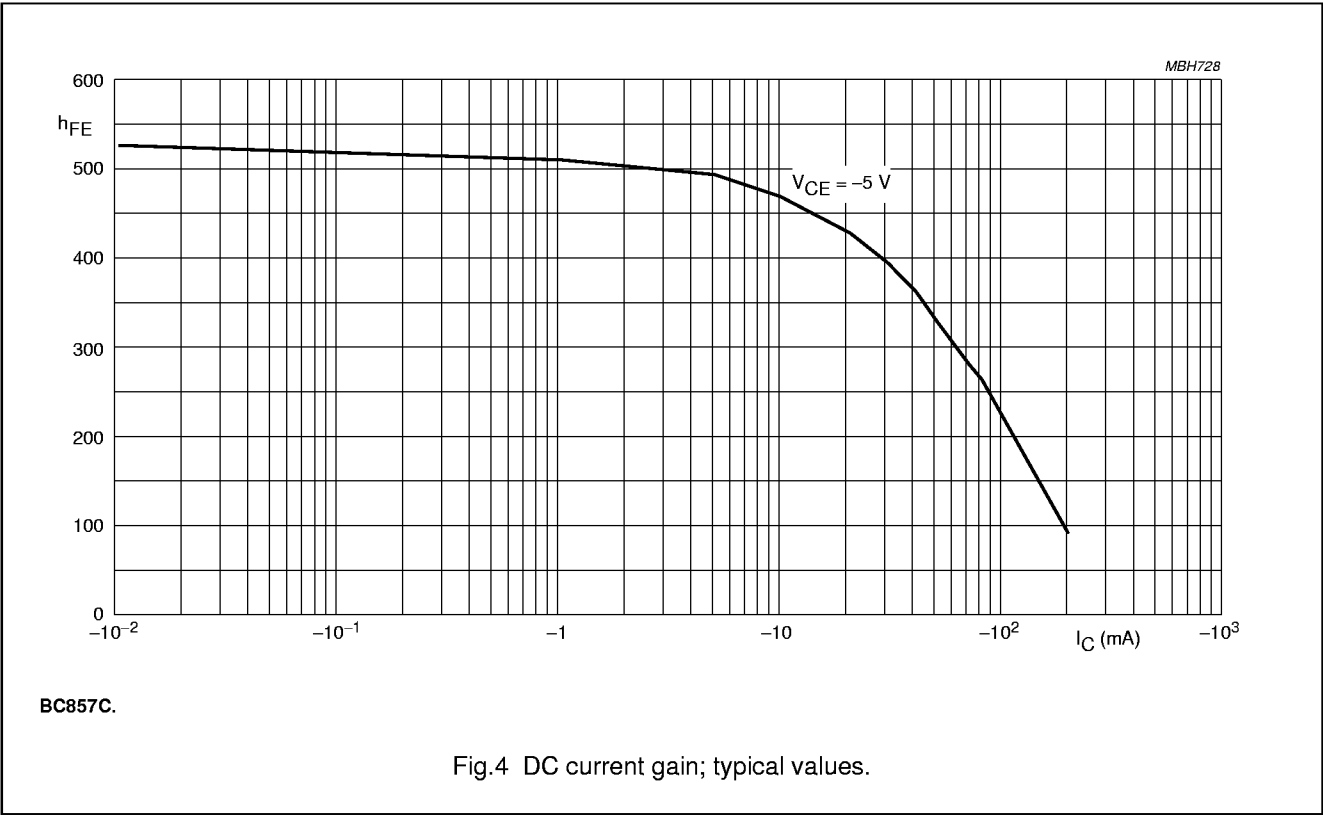
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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23

